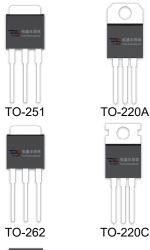


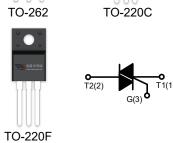
DESCRIPTION:

The BT137X-600E SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.



MAIN FEATURES

Symbol	Symbol Value	
I _{T(RMS)}	8	А
V _{DRM} /V _{RRM}	600 and 800	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40-150	$^{\circ}$
Operating junction temperature range		Tj	-40-125	$^{\circ}$
Repetitive peak off-state voltage(T _j =25℃)		V _{DRM}	600/800	V
Repetitive peak reverse voltage(Tj=25℃)		V_{RRM}	600/800	V
RMS on-state current	TO-251/ TO-220A(Non-Ins)/ TO-220C(Tc=95°C) TO-262/ TO-220A(Ins)/ TO-220F(Ins) (Tc=85°C)	I _{T(RMS)}	8	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		ITSM	65	А
I ² t value for fusing (tp=10ms)		l ² t	21	A ² s
Peak gate current		I _{GM}	2	А



Critical rate of rise of on-state	I - II -III	dl/dt	50	A /u.o
current(I _G =2×I _{GT})	IV	ai/at	10	A/µs
Average gate power dissipation	P _{G(AV)}	0.5	W	
Peak gate power	P _{GM}	5	W	

ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant		Value			l lmi4	
				D	Е	F	G	Unit
l _{GT}	V _D =12V R _L =30Ω	I - II -III	MAX	5	10	25	50	mA
		IV		10	25	70	100	
V _G T		ALL	MAX		1	.3		V
V _{GD}	$V_D=V_{DRM}T_j=125$ °C RL=3.3KΩ	ALL	MIN	0.2			V	
IL	Ig=1.2Igт	I -III	MAX	10	20	50	70	mA
		II -IV		20	30	70	100	
Ін	I _T =100mA		MAX	10	15	40	60	mA
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125℃		MIN	20	50	50	200	V/µs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V _{TM}	I _{тм} =10A tp=380µs	T _j =25℃	1.6	V
IDRM	VD=VDRM VR=VRRM	T _j =25℃	5	μA
IRRM		T _j =125℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	junction to case(AC)	TO-251	2.1	
		TO-220A(Non-Ins)/ TO-220C	1.8	°C/W
		TO-220A(Ins)/ TO-220F(Ins)	2.9	
		TO-262	3.1	



FIG.1: Maximum power dissipation versus RMS on-state current

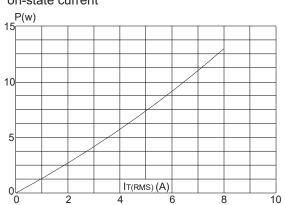


FIG.3: Surge peak on-state current versus number of cycles

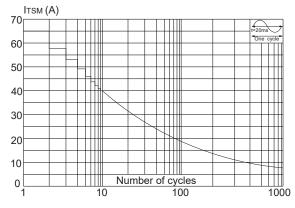


FIG.2: RMS on-state current versus case temperature

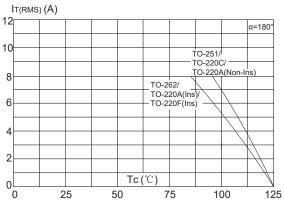


FIG.4: On-state characteristics (maximum values)

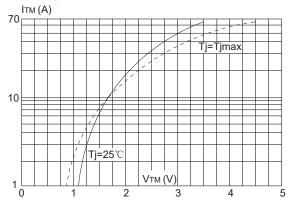




FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t ($I - II - III : dI/dt < 50A/\mu s$; $IV : dI/dt < 10A/\mu s$)

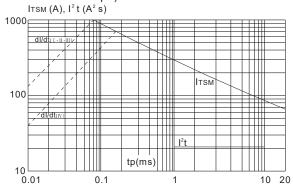


FIG.7: Relative variations of holding current versus junction temperature

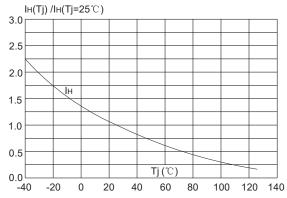


FIG.6: Relative variations of gate trigger current versus junction temperature

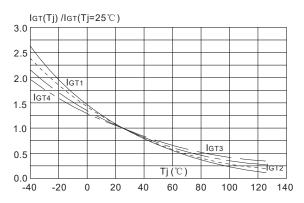


FIG.8: Relative variations of latching current versus junction temperature

